

AMENDMENTS TO THE CLAIMS

1-6. (Cancelled)

7. (Previously Presented) A method for preventing an array substrate from being damaged due to an electrostatic force after a dry-etching process, comprising:

providing a dry-etching apparatus having:

a) a process chamber having a gas inlet, the gas inlet allowing a reactive gas into the process chamber;

b) a first electrode arranged at a predetermined location in the process chamber;

c) a second electrode in the chamber spaced apart from and opposite to the first electrode, having an insulating tape thereon, a plurality of lift pins received in a plurality of holes, the insulating tape being arranged between the plurality of the lift pins, wherein said insulating tape is selected for having characteristics which do not lower a degree of vacuum, said insulating tape distancing the array substrate and the second electrode such that the distance reduces an electrostatic attraction between the second electrode and the array substrate prior to a lifting of the array substrate; and

d) a power source for applying voltages to the first and second electrodes;
arranging the array substrate on the second electrode;
dry-etching the array substrate; and
separating the array substrate from the second electrode using the lift pins.

8. (Original) The method of claim 7, wherein the process chamber is a vacuum chamber.

9. (Original) The method of claim 7, wherein the insulating tape is a vacuum tape.

10. (Original) The method of claim 7, wherein the power source generates RF (radio frequency) power.

11. (Original) The method of claim 7, further comprising DC (direct current) power source for applying DC voltages to the first and second electrodes.

12. (Original) The method of claim 7, wherein the dry-etching process is a plasma dry-etching.

13. (Original) The method of claim 7, wherein the dry-etching process is an ion beam milling etching.

14. (Original) The method of claim 7, wherein the dry-etching process is a reactive ion etching.

15. (Previously Presented) A method for preventing an array substrate from being damaged due to an electrostatic force after a dry-etching process, comprising:

providing a dry-etching apparatus having a first and a second electrodes in a process chamber, the second electrode having a plurality of holes and lift pins, and an insulating tape thereon, wherein said insulating tape is selected for having characteristics which do not lower a degree of vacuum, said insulating tape distancing the array substrate and the second electrode such that the distance reduces an electrostatic attraction between the second electrode and the array substrate prior to a lifting of the array substrate;

arranging the array substrate on the second electrode;

dry-etching the array substrate; and

separating the array substrate from the second electrode using the lift pins.

16. (Original) The method of claim 15, wherein the insulating tape is a vacuum tape.

17. (Currently Amended) A method of processing a substrate for a liquid crystal display (LCD) device, the method comprising:

providing an electrode plate;

providing an intermediate material selected for having characteristics which do not lower a degree of vacuum, on the surface of the electrode plate;

positioning a substrate at a predetermined distance from the electrode plate to obtain an intermediate structure, wherein said positioning reduces electrostatic attraction between said substrate and said electrode plate prior to a lifting of said substrate;

processing the intermediate structure; and

removing the substrate from the electrode plate.

18. (Cancelled)

19. (Currently Amended) The method of claim 17, wherein the substrate is positioned at the predetermined distance from the electrode plate by placing ~~an~~ the intermediate material between the substrate and the electrode plate.

20. (Previously Presented) A method of processing a substrate for a liquid crystal display (LCD) device, the method comprising:

providing an electrode;

providing an intermediate material on the electrode;

providing a substrate on the intermediate material of the electrode to obtain an intermediate structure;

processing the intermediate structure; and

removing the substrate from the electrode utilizing a plurality of pins formed on the electrode to push the substrate away from the electrode, wherein the intermediate material is selected for having characteristics which do not lower a degree of vacuum, said intermediate material distancing the substrate and the electrode such that the distance reduces electrostatic attraction between the substrate and the electrode prior to a lifting of the substrate.

21-23. (Cancelled)